

L Number	Hits	Search Text	DB	Time stamp
1	3	365/189.09, 189.11, 230.06, 201, 226, 190, 203-2 and (bias with generator) same SRAM same test\$3	US-PAT; 154, 1 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 07:33
2	22	365/189.09, 189.11, 230.06, 201, 226, 190, 203-2 and (bias with generator) same SRAM	US-PAT; 154, 1 US-PGPUB;	2004/07/15 07:35
3	20	(adjust\$3 with bias) same (test with memory)	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/07/15 07:36
4	4	365/201.cc1s. and (adjust\$3 with bias) same (test with memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/07/15 07:37
5	96	365/\$.cc1s.. and (((pull-up or pull-down) with transistor) or (metal with program\$4)) and (adjust\$4 or level\$) and bias same voltage same test\$4 and (SRAM or (static with random with access memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 07:39
6	56	365/189.09, 189.11, 230.06, 201, 226, 190, 203-2 and ((pull-up or pull-down) with transistor) or (metal with program\$4)) and (adjust\$4 or level\$) and bias same voltage same test\$4 and (SRAM or (static with random with access memory))	US-PAT; 154, 1 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 07:39
7	29	365/189.09, 189.11, 230.06, 201, 226, 190, 203-2 and ((pull-up or pull-down) with transistor) or (metal with program\$4)) and (adjust\$4 or level\$) same bias same voltage same test\$4 and (SRAM or (static with random with access memory))	US-PAT; 154, 1 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/07/15 07:39
-	6	365/189.09, 189.11, 230.06, 201, 226, 190, 203-2 and ((pull-up or pull-down) with transistor) or (metal with program\$4)) and (adjust\$4 or level\$) same bias same voltage same test\$4 and (SRAM or (static with random with access memory))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/07/15 07:32
-	14	(bias with generator) and SRAM and voltage same output same signal and (metal with program\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/07/03 16:12
-	1	((Blaine with Stackhouse) and (Hewlett with packard with development with company))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/07/03 16:20
-	4	((Blaine with Stackhouse) or (Hewlett with packard with development with company)) and (bias with generator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/07/03 16:22
-	103	((Blaine with Stackhouse) or (Hewlett with packard with development with company)) and 365/\$.cc1s.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/07/03 16:22
-	27	((Blaine with Stackhouse) or (Hewlett with packard with development with company)) and 365/\$.cc1s. and bias	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/03 16:55

-	10	((Blaine with Stackhouse) or (Hewlett with packard with development with company)) and 365/\$.ccls. and bias and metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/03 16:24
-	3	365/\$.ccls. and (bias with generator) same transistor same metal	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/03 17:00
-	66	(bias with generator) same transistor same metal	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/03 17:00
-	1	(bias with generator) same transistor same metal same program\$4	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/03 17:01
-	2	365/230.06,201,226,190,203-205,194,154,156 and (bias with generator) same transistor same metal	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/15 07:32
-	12	program\$4 with bias with test\$4 and SRAM	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/06 18:01
-	3	((pull-up or pull-down) with transistor) same bias same test\$4 and SRAM	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/07 09:26
-	6	((pull adj up) or (pull adj down) with transistor) same bias same test\$4 and SRAM	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/06 18:05
-	16	((pull-up or pull-down) with transistor) or (metal with program\$4) same (adjust\$4 or levels) same bias same test\$4	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/07 10:41
-	17	("4916668"   "4967395"   "5132575"   "5245578"   "5302870"   "5369317"   "5555523"   "5677886"   "5680344"   "5701268"   "5732033"   "5862089"   "5877993"   "5912853"   "5991216"   "6052322"   "6157586").PN.	IBM_TDB USPAT	2004/07/07 09:32
-	4	6499081.URPN.	USPAT	2004/07/07 09:46
-	3	(SRAM or (static with random with access with memory)) and adjust\$ same magnitude\$1 same bias same test\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/07 09:51
-	6	(SRAM or (static with random with access with memory)) and adjust\$ same magnitude\$1 same bias and test\$3	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/07 09:52
-	35	365/230.06,201,226,190,203-205,194,154,156 and (SRAM or (static with random with access with memory)) and (adjust\$ or ((pull adj up) and (pull adj down) with transistor)) same magnitude\$1 and test\$3	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/07 10:20

-	-	16	365/230.06,201,226,190,203-205,194,154,156 and (adjust\$ or ((pull adj up) and (pull adj down) with transistor)) same magnitude\$1 and test\$3 and (SRAM or (static with random with access with memory)) and (adjust\$ or ((pull adj up) and (pull adj down) with transistor)) same (magnitude\$1 with bias with voltage) and test\$3 and (SRAM or (static with random with access with memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:21
-	-	1	365/230.06,201,226,190,203-205,194,154,156 and (SRAM or (static with random with access with memory)) and (adjust\$ or ((pull adj up) and (pull adj down) with transistor)) same (magnitude\$1 with bias with voltage) and test\$3 and (SRAM or (static with random with access with memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/07 10:06
-	-	2	365/230.06,201,226,190,203-205,194,154,156 and (SRAM or (static with random with access with memory)) and (adjust\$ or ((pull adj up) and (pull adj down) with transistor)) same magnitude\$1 and test\$3 and "4061668" with "5132575"   "5245578"   "5302870"   "5369317"   "5555523"   "5677886"   "5680344"   "5701268"   "5732033"   "5862089"   "5877993"   "5912853"   "5991216"   "6052322"   "6157586").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/07 10:21
-	-	17	365/230.06,201,226,190,203-205,194,154,156 and "4061668" with "5132575"   "5245578"   "5302870"   "5369317"   "5555523"   "5677886"   "5680344"   "5701268"   "5732033"   "5862089"   "5877993"   "5912853"   "5991216"   "6052322"   "6157586").PN.	USPAT	2004/07/07 10:32
-	-	14	((pull-up or pull-down) with transistor) or (metal with program\$4) same (adjust\$4 or level\$) same bias same test\$4 and (SRAM or (static with random with access memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:01
-	-	2	((pull-up or pull-down) with transistor) or (metal with program\$4) same (adjust\$4 or level\$) same bias same test\$4 and (SRAM or (static with random with access memory)) and weak	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/07 12:09
-	-	14	((pull-up or pull-down) with transistor) or (metal with program\$4) same (adjust\$4 or level\$) same bias same voltage same test\$4 and (SRAM or (static with random with access memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 10:12
-	-	4	(bias with generator) and ((pull-up or pull-down) with transistor) or (metal with program\$4) same (adjust\$4 or level\$) same bias same voltage same test\$4 and (SRAM or (static with random with access memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 10:13
-	-	96	365/.cc1s. and ((pull-up or pull-down) with transistor) or (metal with program\$4) and (adjust\$4 or level\$) and bias same voltage same test\$4 and (SRAM or (static with random with access memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:16
-	-	227	365/.cc1s. and ((pull-up or pull-down) with transistor) or (metal with program\$4) and (adjust\$4 or level\$) and (bias with voltage) and test\$4 and (SRAM or (static with random with access memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:17
-	-	16	365/.cc1s. and ((pull-up or pull-down) with transistor) or (metal with program\$4) and (adjust\$4 or level\$) and (bias with voltage with output with signal) and test\$4 and (SRAM or (static with random with access memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 10:41
-	-	35	365/230.06,201,226,190,203-205,194,154,156 and (adjust\$ or ((pull adj up) and (pull adj down) with transistor)) same magnitude\$1 and test\$3 and (SRAM or (static with random with access with memory)) and SRAM and adjust\$3 with magnitude	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:24
-	-	11	365/230.06,201,226,190,203-205,194,154,156 and (adjust\$ or ((pull adj up) and (pull adj down) with transistor)) same magnitude\$1 and test\$3 and (SRAM or (static with random with access with memory)) and SRAM and adjust\$3 with magnitude	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 10:54

-	69	((pull-up or pull-down) with transistor) or program\$4 same (adjust\$4 or chang\$3) same bias same voltage\$1 same test\$4 and (SRAM or (static with random with access memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 12:48
-	19	365/\$.cccls. and (((pull-up or pull-down) with transistor) or program\$4) same (adjust\$4 or chang\$3) same bias same voltage\$1 same test\$4 and (SRAM or (static with random with access memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:10
-	21	365/\$.cccls. and (((pull-up or pull-down) with transistor) or program\$4) same (adjust\$4 or chang\$3 or modif\$7) same bias same voltage\$1 same test\$4 and (SRAM or (static with random with access memory))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:12
-	4	365/\$.cccls. and (((pull-up or pull-down) with transistor) or program\$4) same (adjust\$4 or chang\$3 or modif\$7) same bias same voltage\$1 same test\$4 and (SRAM or (static adj random adj access adj memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:12
-	57	(program\$4 and bias and test\$4 and SRAM) aND (365/\$.cccls. and (((pull-up or pull-down) with transistor) or (metal with program\$4)) and (adjust\$4 or level\$) and (bias with voltage) and test\$4 and (SRAM or (static adj random adj access memory)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:20
-	1	365/230.06, 201, 226, 190, 203-205, 194, 154, 156 and (adjust\$ OR CHANG\$3 or modif\$7 or ((pull adj up) and (pull adj down) with transistor)) same magnitude\$1 same bias same voltage and test\$3 and (SRAM or (static adj random adj access adj memory)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:23
-	34	365/230.06, 201, 226, 190, 203-205, 194, 154, 156 and (adjust\$ or ((pull adj up) and (pull adj down) with transistor)) same magnitude\$1 and test\$3 and (SRAM or (static adj random adj access adj memory)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:28
-	4	365/230.06, 201, 226, 190, 203-205, 194, 154, 156 and (adjust\$ or ((pull adj up) and (pull adj down) with transistor)) same magnitude\$1 and test\$3 and (SRAM or (static adj random adj access adj memory))) and (365/230.06, 201, 226, 190, 203-205, 194, 154, 156 and (adjust\$ or ((pull adj up) and (pull adj down) with transistor)) same magnitude\$1 and test\$3 and (SRAM or (static adj random adj access adj memory)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:24
-	69	365/230.06, 201, 226, 190, 203-205, 194, 154, 156 and (adjust\$ or chang\$3 or modif\$7 or ((pull adj up) and (pull adj down) with transistor)) same magnitude\$1 and test\$3 and (SRAM or (static adj random adj access adj memory)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:29
-	1	365/230.06, 201, 226, 190, 203-205, 194, 154, 156 and (adjust\$ or chang\$3 or modif\$7 or ((pull adj up) and (pull adj down) with transistor)) same magnitude\$1 same bias same voltage and test\$3 and (SRAM or (static adj random adj access adj memory)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:30
-	3	365/230.06, 201, 226, 190, 203-205, 194, 154, 156 and (adjust\$ or chang\$3 or modif\$7) same ((pull adj up) and (pull adj down) with transistor) same bias same voltage and (test\$3 with (SRAM or (static adj random adj access adj memory)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:34
-	5	((pull-up or pull-down) with transistor) or program\$4 same (supply with voltage) same (bias with generator) same output and test\$4 and (SRAM or (static with random with access memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 12:53